

SOT-23 Plastic-Encapsulate Diodes

CMPSH-3 SCHOTTKY BARRIER DIODE

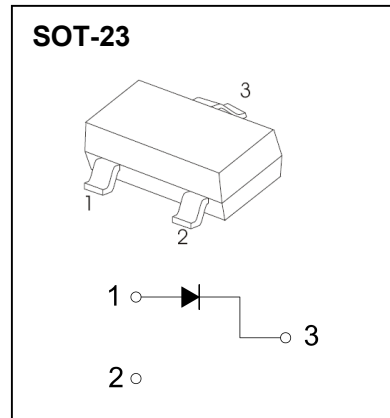
FEATURES

- High Switching Speed
- Low Forward Voltage

MARKING: D95

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{RRM}	Peak Repetitive Reverse Voltage	30	V
I_O	Continuous Forward Current	100	mA
I_{FRM}	Peak Repetitive Forward Current	350	mA
I_{FSM}	Non-repetitive Peak Forward Current @ $t_p=10\text{ms}$	750	mA
P_D	Power Dissipation	350	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	286	$^{\circ}\text{C}/\text{W}$
T_j	Junction Temperature	125	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^{\circ}\text{C}$



ELECTRICAL CHARACTERISTICS($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse voltage	$V_{(BR)}$	$I_R=100\mu\text{A}$	30			V
Reverse current	I_R	$V_R=25\text{V}$			0.5	μA
Forward voltage	V_F	$I_F=2\text{mA}$			0.33	V
		$I_F=15\text{mA}$			0.45	
		$I_F=100\text{mA}$			1	
Total capacitance	C_{tot}	$V_R=1\text{V}, f=1\text{MHz}$		7		pF
Reverse recovery time	t_{rr}	$I_F=I_R=10\text{mA}, I_{tr}=0.1\times I_R, R_L=100\Omega$		5		ns